



Docket No.: 57810-076

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	Customer Number: 20277
	:	
Daijiro INOUE, et al.	:	Confirmation Number: 2234
	:	
Serial No.: 10/663,714	:	Group Art Unit: 2811
	:	
Filed: September 17, 2003	:	Examiner:
	:	
For: NITRIDE-BASED SEMICONDUCTOR LIGHT-EMITTING DEVICE	:	

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

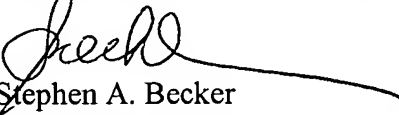
This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Serial No.:

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Date: December 23, 2003



SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)			ATTY. DOCKET NO. 57810-076		SERIAL NO. 10/663,714		
			APPLICANT Daijiro INOUE, et al.				
			FILING DATE September 17, 2003		GROUP 2811		
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US					
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code ³ -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 2001-60720 A	03/06/2001	TOSHIBA CORP.		JAPAN (w/English Abstract)	
		JP 2002-124737	04/26/2002	SANYO ELECTRIC CO LTD		JAPAN (w/English Abstract)	
		JP 2002-299768	10/11/2002	MATSUSHITA ELECTRIC IND CO LTD		JAPAN (w/English Abstract)	
		JP 2001-57461	02/27/2001	NICHIA CHEM IND LTD		JAPAN (w/English Abstract)	
		JP 11-340580	12/10/1999	FUJITSU LTD		JAPAN (w/English Abstract)	
		JP 10-294529	11/4/1998	TOSHIBA CORP.		JAPAN (w/English Abstract)	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		T. Asano, et al. " High-power 400-nm-band AlGaInN-based laser diodes with low aspect ratio." Applied Physics Letters, Volume 80, Number 19, May 13, 2002, pp.3497-3499					
		Nishinaga Tatau, " Hetero-epitaxy with Large Lattice Mismatch and Microchannel Epitaxy of Compound Semiconductor." Department of Electronic Engineering, Graduate School of Engineering, Volume 21, No. 6, pp. 320-325, 2000					
		Takashi Mizuno, et al. " High power Blue-violet Laser Diodes." The Institute of Electronics, Information and Communication Engineers, Technical Report of IEICE. ED2002-112, LQE2002-87 (2002-06), pp. 63-66					
		H. Amano, et al. " Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AlN buffer layer." Appl. Phys. Lett., Vol. 48, No. 5, 3 February 1986. pp. 353-355					
EXAMINER				DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.